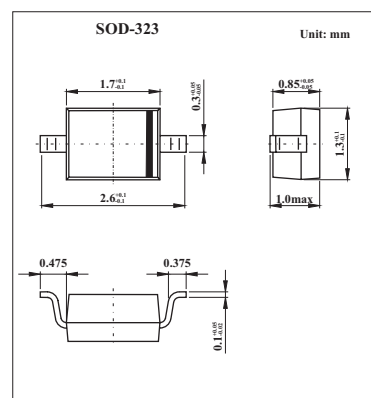


Silicon Schottky Diode

BAT62-03W

■ Features

- Low Barrier diode for detectors up to GHz frequencies



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V _R	40	V
Forward current	I _F	40	mA
Junction current	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
Total power dissipation	P _{tot}	100	mW
Junction ambient ⁽¹⁾	R _{thJA}	≤ 650	K/W
Junction-soldering point	R _{thJS}	≤ 810	K/W

Note:

1. Package mounted on an epoxy pcb 15 mm × 16.7mm × 0.7 mm

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Breakdown current	I _R	V _R = 40 V, T _A = 25 °C			10	μ A
Forward voltage	V _F	I _F = 2 mA		0.58	1	V
Diode capacitance	C _T	V _R = 0; f = 1 MHz		0.35	0.6	pF
Case capacitance	C _C	f = 1 MHz		0.1		pF
Differential forward resistance	R _O	V _R = , f = 10 kHz		225		k Ω
Series inductance chip to ground	L _s			2		nH

■ Marking

Marking	L
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